

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	3271	(nitride or "silicon nitride" or SiN or "Si.sub.3 N.sub.4") near7 implant\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	2748	oxide and 1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	2689	@ad<=20011105 and 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	4823 6	emitter and collector and base and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	4252	oxide and 1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	862	implant\$4 and 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	853	@ad<=20011105 and 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB